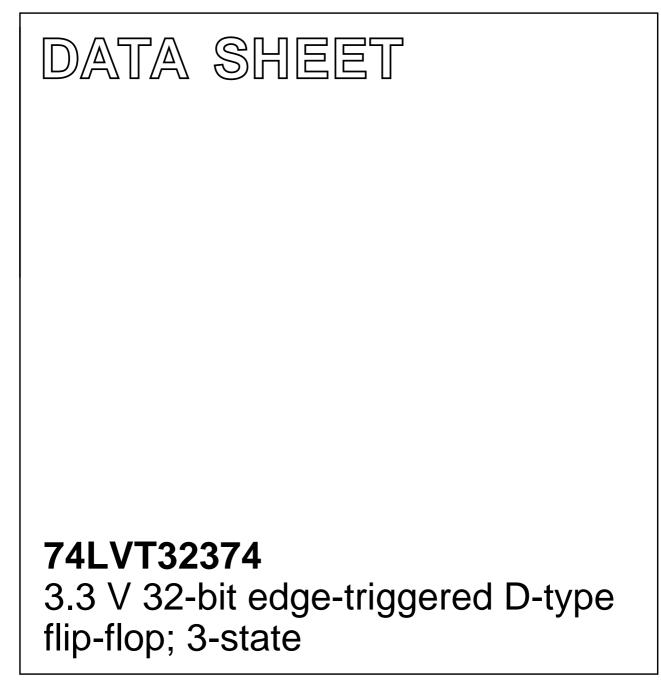
INTEGRATED CIRCUITS



Product specification Supersedes data of 2002 Mar 20 2004 Oct 15



Product specification

3.3 V 32-bit edge-triggered D-type flip-flop; 3-state

74LVT32374

FEATURES

- 32-bit edge-triggered flip-flop
- 3-state buffers
- Output capability: +64 mA/-32 mA
- · TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- · Bus-hold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- · Power-up reset
- Power-up 3-state
- · No bus current loading when output is tied to 5 V bus
- Latch-up protection exceeds 500 mA in accordance with JEDEC std 17
- ESD protection exceeds 2000 V in accordance with MIL STD 883 method 3015 and 200 V in accordance with machine model.

QUICK REFERENCE DATA

Co

I_{CCZ}

GND = 0 V; $T_{amb} = 25 \text{ °C}$; $t_r = t_f \le 2.5 \text{ ns}$.

output capacitance

total supply current

SYMBOL PARAMETER CONDITIONS **TYPICAL** UNIT propagation delay nCP to nQn $C_{L} = 50 \text{ pF}; V_{CC} = 3.3 \text{ V}$ 2.9 ns t_{PHL}/t_{PLH} $V_{I} = 0 V \text{ or } 3.0 V$ CI input capacitance 3 pF

outputs disabled; $V_{O} = 0 V \text{ or } 3.0 V$

output disabled; $V_{CC} = 3.6 V$

DESCRIPTION

The 74LVT32374 is a high-performance BICMOS product designed for V_{CC} operation at 3.3 V.

The 74LVT32374 is a 32-bit edge-triggered D-type flip-flop featuring non-inverting 3-state outputs. The device can be used as four 8-bit flip-flops, or two 16-bit flip-flops or one 32-bit flip-flop. On the positive transition of the clock (CP), the Q outputs of the flip-flop take on the logic levels set-up at the D inputs.

9

140

pF

μΑ

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FUNCTION TABLE

See note 1.

OPERATING MODE		INPUT		INTERNAL	OUTPUT
OPERATING MODE	nOE	nCP	nD _n	REGISTER	nQ _n
Load and read register	L	↑	I	L	L
	L	↑	h	Н	Н
Hold	L	1	Х	NC	NC
Disable outputs	Н	Ļ	Х	NC	Z
	Н	↑	nD _n	nD _n	Z

Note

1. H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the HIGH-to-LOW OE transition;

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the HIGH-to-LOW OE transition;

NC = not connected;

X = don't care;

Z = high-impedance OFF-state;

- \uparrow = LOW-to-HIGH CP transition;
- = not a LOW-to-HIGH CP transition.

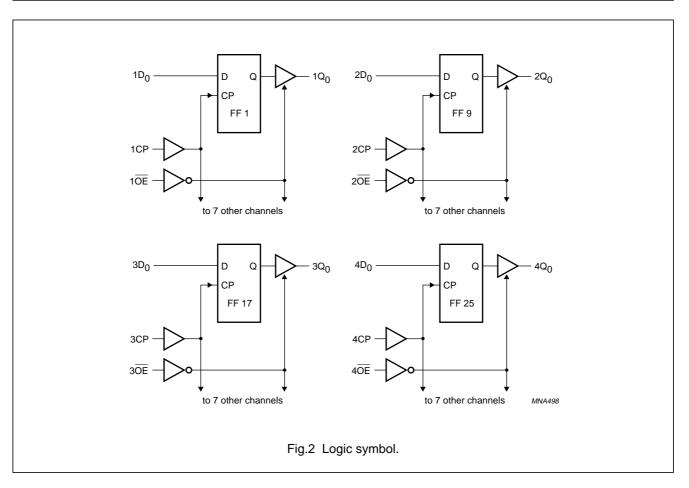
ORDERING INFORMATION

TYPE NUMBER	TEMPERATURE	URE PACKAGE					
I TPE NUMBER	RANGE	PINS	PACKAGE	MATERIAL	CODE		
74LVT32374EC	–40 °C to +85 °C	96	LFBGA96	plastic	SOT536-1		

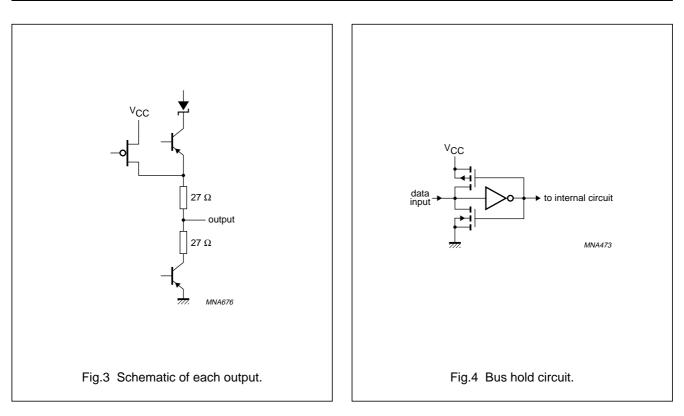
PINNING

SYMBOL	DESCRIPTION
nD _n	data input
nCP	clock input
nQ _n	flip-flop output
GND	ground (0 V)
nOE	output enable input (active LOW)
V _{CC}	supply voltage

6	1D ₁	10	10	10	20	20	20	20	2D	20	2D	20	40	40		MNA497
0	1	1D ₃	1D ₅	1D ₇	2D1	2D3	2D5	2D ₇	3D ₁	3D3	3D ₅	3D7		4D3		4D ₆
5	1D ₀	1D ₂	1D ₄	1D ₆	2D ₀	2D ₂	2D ₄	2D ₆	3D ₀	3D ₂	3D ₄	3D ₆	4D ₀	4D ₂	4D ₄	4D ₇
4	1CP	GND	V _{CC}	GND	GND	V _{CC}	GND	2CP	3CP	GND	V _{CC}	GND	GND	Vcc	GND	4CP
3	10E	GND	Vcc	GND	GND	V _{CC}	GND	20E	3 0E	GND	Vcc	GND	GND	Vcc	GND	40E
2	1Q ₀	1Q ₂	1Q ₄	1Q ₆	2Q ₀	2Q ₂	2Q ₄	2Q ₆	зQ ₀	3Q ₂	3Q ₄	3Q ₆	4Q ₀	4Q2	4Q4	4Q7
1	1Q ₁	1Q ₃	1Q ₅	1Q ₇	2Q ₁	2Q ₃	2Q ₅	2Q ₇	3Q ₁	3Q3	3Q ₅	3Q ₇	4Q ₁	4Q3	4Q ₅	4Q ₆
	A	В	С	D	E	F	G	н	J	к	L	М	N	Р	R	т



74LVT32374



RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		2.7	+3.6	V
VI	input voltage	note 1	0	5.5	V
V _{IH}	HIGH-level input voltage		2.0	_	V
V _{IL}	LOW-level input voltage		_	0.8	V
I _{OH}	HIGH-level output current		-	-32	mA
I _{OL}	LOW-level output current		-	32	mA
		current duty cycle \leq 50 %; f \geq 1 kHz	_	64	mA
$\Delta t / \Delta V$	input transition rise or fall times	outputs enabled	-	10	ns/V
T _{amb}	ambient temperature		-40	+85	°C
P _{tot}	power dissipation per package	note 2	_	1000	mW

Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. Above 70 $^\circ\text{C}$ the value of P_{tot} derates linearly with 1.8 mW/K.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); note 1.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	-	+4.6	V
I _{IK}	input diode current V ₁ < 0 V		_	-50	_	mA
VI	input voltage	note 2	-0.5	-	+7.0	V
I _{ОК}	output diode current		_	-50	-	mA
Vo	output voltage	output in OFF or HIGH state; note 2	-0.5	-	+7.0	V
lo	output current	output in LOW state	-	128	_	mA
		output in HIGH state	_	-64	_	mA
T _{stg}	storage temperature		-65	-	+150	°C

Notes

1. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

2. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

3-state

DC CHARACTERISTICS

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

OVMDO	DADAMETED	TEST CONDITIONS						
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.		
T _{amb} = -40) °C to +85 °C				-			
V _{IK}	input clamp voltage	I _{IK} = –18 mA	2.7	-	-0.85	-1.2	V	
V _{OH}	HIGH-level output voltage	I _{OH} = -32 mA	3.0	2.0	2.3	-	V	
V _{OL}	LOW-level output voltage	I _{OL} = 64 mA	3.0	-	0.4	0.55	V	
V _{RST}	power-up output LOW voltage	$I_O = -1 \text{ mA}; V_I = \text{GND or } V_{CC};$ note 2	3.6	-	0.1	0.55	V	
ILI	input leakage current	$V_I = V_{CC}$ or GND; control pins	3.6	-	0.1	±1	μA	
		V _I = 5.5 V	0 or 3.6	-	0.4	10	μA	
		$V_{I} = V_{CC}$; data pins; note 3	3.6	_	0.1	1	μA	
		V _I = 0 V; data pins; note 3	3.6	-	-0.4	-5	μA	
I _{off}	output OFF current	$V_1 \text{ or } V_0 = 0 \text{ V to } 4.5 \text{ V}$	0	-	0.1	±100	μA	
I _{hold}	bus hold current D inputs	V _I = 0.8 V; note 4	3.0	75	135	_	μA	
		V _I = 2.0 V; note 4	3.0	-75	-135	-	μA	
		V _{CC} = 3.6 V; note 4	0 to 3.6	±500	-	-	μA	
I _{EX}	current into an output in the HIGH state when $V_O > V_{CC}$	V _O = 5.5 V	3.0	-	50	125	μA	
I _{pu/pd}	power-up/down 3-state output current	$V_O = 5.5 V$ to V_{CC} ; $V_I = GND$ or V_{CC} ; $V_{OE} =$ don't care; note 5	≤ 1.2 V	_	1	±100	μA	
I _{OZH}	3-state output HIGH current	$V_0 = 3.0 \text{ V}; \text{ V}_1 = \text{V}_{1H} \text{ or } \text{V}_{1L}$	3.6	-	0.5	5	μA	
I _{OZL}	3-state output LOW current	$V_0 = 0.5 \text{ V}; \text{ V}_1 = \text{V}_{1H} \text{ or } \text{V}_{1L}$	3.6	-	+0.5	-5	μA	
I _{ССН}	quiescent supply current	outputs HIGH; $I_0 = 0 A$; V ₁ = GND or V _{CC}	3.6	-	0.14	0.24	mA	
I _{CCL}	quiescent supply current	outputs LOW; $I_0 = 0 A$; V _I = GND or V _{CC}	3.6	-	8	12	mA	
I _{CCZ}	quiescent supply current	outputs disabled; $I_0 = 0 A$; V ₁ = GND or V _{CC} ; note 6	3.6	-	0.14	0.24	mA	
ΔI_{CC}	additional supply current per input pin	one input at V_{CC} – 0.6 V; other inputs at GND or V_{CC} ; note 7	3.0 to 3.6	-	0.1	0.2	μA	

Notes

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

- 2. For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.
- 3. Unused pins at V_{CC} or GND.
- 4. This is the bus hold overdrive current required to force the input to the opposite logic state.
- 5. This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 µs is permitted. This parameter is valid for T_{amb} = 25 °C only.
- 6. I_{CCZ} is measured with outputs pulled to V_{CC} or GND.
- 7. This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

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Product specification

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AC CHARACTERISTICS

 $GND = 0 \text{ V}; \text{ } t_{r} = t_{f} \leq 2.5 \text{ ns}; \text{ } C_{L} = 50 \text{ pF}; \text{ } R_{L} = 500 \text{ } \Omega.$

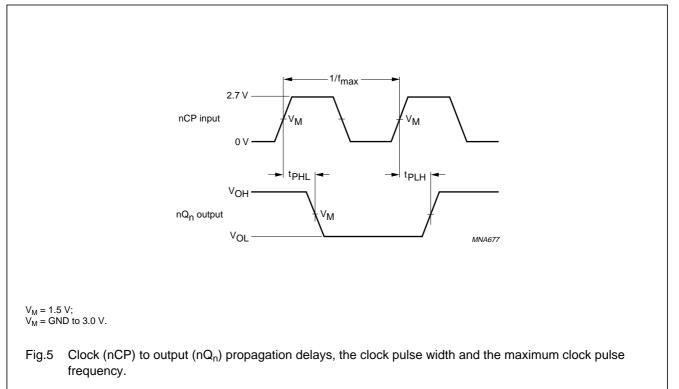
OVMDO		CONDITIC	RAINI					
SYMBOL	PARAMETER	WAVEFORMS	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	UNIT	
T _{amb} = -40	°C to +85 °C			ł		-		
t _{PLH}	propagation delay	see Fig.5	2.7	-	-	6.2	ns	
	nCP to nQ _n		3.0 to 3.6	1.5	3.0	5.3	ns	
t _{PHL}	propagation delay	see Fig.5	2.7	-	_	5.1	ns	
	nCP to nQ _n		3.0 to 3.6	1.5	3.0	4.9	ns	
t _{PZH}	output enable time to	see Figs 7 and 8	2.7	-	_	6.9	ns	
	HIGH level		3.0 to 3.6	1.5	3.5	5.6	ns	
• == •	output enable time to	see Figs 7 and 8	2.7	-	-	6.0	ns	
	LOW level		3.0 to 3.6	1.5	3.2	4.9	ns	
t _{PHZ} output disable HIGH level	output disable time from	see Figs 7 and 8	2.7	-	_	5.7	ns	
	HIGH level		3.0 to 3.6	1.5	3.5	5.4	ns	
t _{PLZ}	output disable time from LOW level	see Figs 7 and 8	2.7	1.5	3.2	5.1	ns	
			3.0 to 3.6	1.5	3.2	5.0	ns	
t _{suH} s	set-up time nD _n HIGH to nCP	see Fig.6	2.7	2.0	-	-	ns	
			3.0 to 3.6	2.0	0.7	-	ns	
t _{suL}	set-up time nD _n LOW to nCP	see Fig.6	2.7	2.0	-	-	ns	
			3.0 to 3.6	2.0	0.7	-	ns	
t _{hH}	hold time	see Fig.6	2.7	0.1	_	-	ns	
	nD _n HIGH to nCP		3.0 to 3.6	0.8	0	-	ns	
t _{hL}	hold time	see Fig.6	2.7	0.1	_	-	ns	
	nD _n LOW to nCP		3.0 to 3.6	0.8	0	-	ns	
t _{WH}	nCP HIGH pulse width	see Fig.6	2.7	1.5	_	-	ns	
			3.0 to 3.6	1.5	0.6	_	ns	
t _{WL}	nCP LOW pulse width	see Fig.6	2.7	3.0	-	-	ns	
			3.0 to 3.6	3.0	1.6	_	ns	
f _{max}	maximum clock pulse frequency	see Fig.5	3.0 to 3.6	150	_	-	MHz	

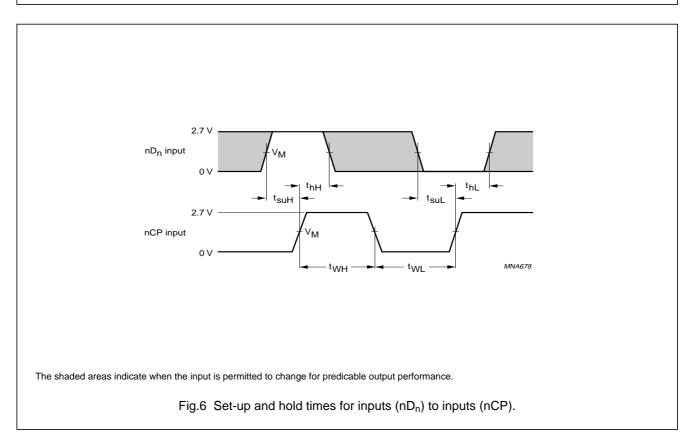
Note

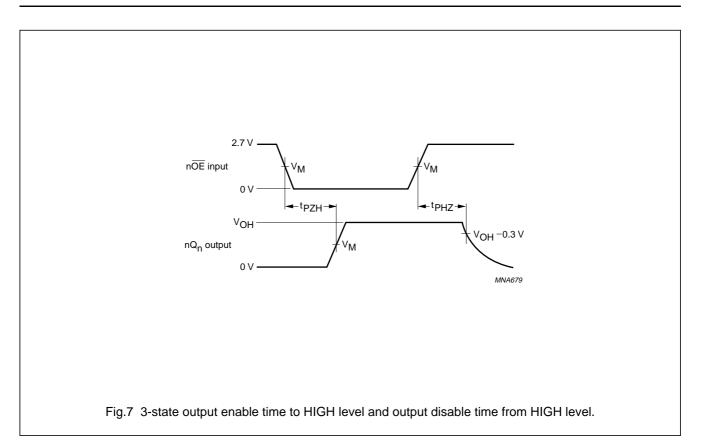
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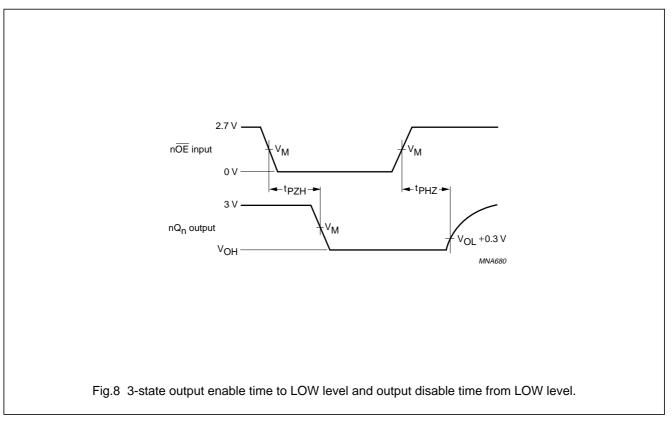
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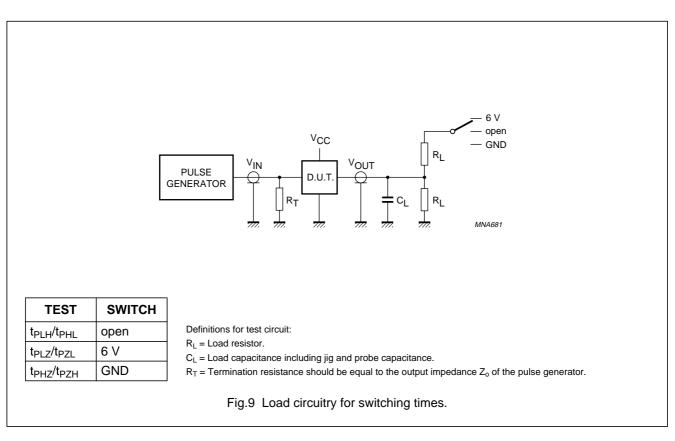
AC WAVEFORMS

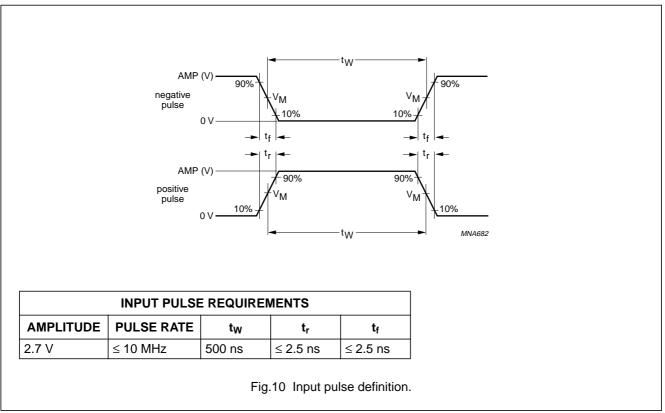






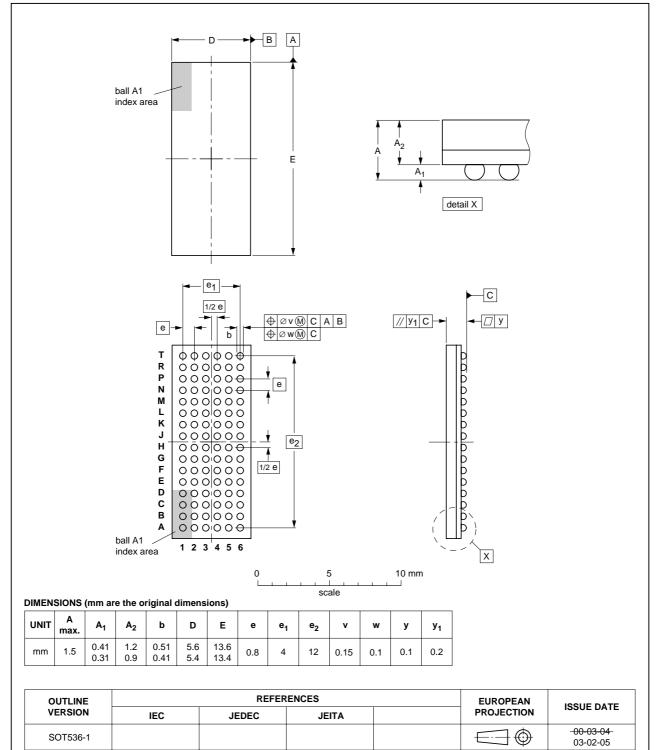






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PACKAGE OUTLINE



LFBGA96: plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 x 5.5 x 1.05 mm SOT536-1

74LVT32374

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
1	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
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DEFINITIONS

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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